

## **Structure of Nonvolatile Memory Array**

### **ABSTRACT OF THE INVENTION**

5           A structure of a nonvolatile memory array with low source  
line sheet resistance is disclosed in this present invention. The key  
aspect of this present invention is employing a buried conductive  
region as the source line of a nonvolatile memory array. The topology  
of the above-mentioned buried conductive region is different from the  
10 source line in the prior art. Therefore, this invention can provide a  
nonvolatile memory array for reducing the source line sheet  
resistance and achieving the reliability and the operating performance  
of the nonvolatile memory array.